



May 2000

QFET™

# FQB4N25 / FQI4N25

## 250V N-Channel MOSFET

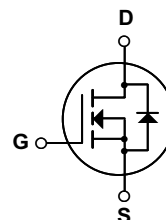
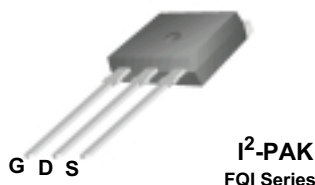
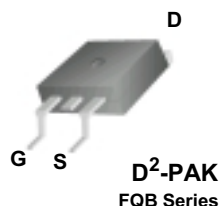
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switching DC/DC converters, switch mode power supply.

### Features

- 3.6A, 250V,  $R_{DS(on)} = 1.75\Omega$  @  $V_{GS} = 10V$
- Low gate charge ( typical 4.3 nC)
- Low  $C_{rss}$  ( typical 4.8 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

| Symbol         | Parameter                                                                     | FQB4N25 / FQI4N25 | Units               |
|----------------|-------------------------------------------------------------------------------|-------------------|---------------------|
| $V_{DSS}$      | Drain-Source Voltage                                                          | 250               | V                   |
| $I_D$          | Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )                       | 3.6               | A                   |
|                | - Continuous ( $T_C = 100^\circ\text{C}$ )                                    | 2.3               | A                   |
| $I_{DM}$       | Drain Current - Pulsed (Note 1)                                               | 14.4              | A                   |
| $V_{GSS}$      | Gate-Source Voltage                                                           | $\pm 30$          | V                   |
| $E_{AS}$       | Single Pulsed Avalanche Energy (Note 2)                                       | 52                | mJ                  |
| $I_{AR}$       | Avalanche Current (Note 1)                                                    | 3.6               | A                   |
| $E_{AR}$       | Repetitive Avalanche Energy (Note 1)                                          | 5.2               | mJ                  |
| dv/dt          | Peak Diode Recovery dv/dt (Note 3)                                            | 5.5               | V/ns                |
| $P_D$          | Power Dissipation ( $T_A = 25^\circ\text{C}$ ) *                              | 3.13              | W                   |
|                | Power Dissipation ( $T_C = 25^\circ\text{C}$ )                                | 52                | W                   |
|                | - Derate above $25^\circ\text{C}$                                             | 0.42              | W/ $^\circ\text{C}$ |
| $T_J, T_{STG}$ | Operating and Storage Temperature Range                                       | -55 to +150       | $^\circ\text{C}$    |
| $T_L$          | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | 300               | $^\circ\text{C}$    |

### Thermal Characteristics

| Symbol          | Parameter                                 | Typ | Max  | Units              |
|-----------------|-------------------------------------------|-----|------|--------------------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case      | --  | 2.4  | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient * | --  | 40   | $^\circ\text{C/W}$ |
| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient   | --  | 62.5 | $^\circ\text{C/W}$ |

\* When mounted on the minimum pad size recommended (PCB Mount)

**Electrical Characteristics** $T_C = 25^\circ\text{C}$  unless otherwise noted

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Units |
|--------|-----------|-----------------|-----|-----|-----|-------|
|--------|-----------|-----------------|-----|-----|-----|-------|

**Off Characteristics**

|                                |                                           |                                                                   |     |      |      |                     |
|--------------------------------|-------------------------------------------|-------------------------------------------------------------------|-----|------|------|---------------------|
| $BV_{DSS}$                     | Drain-Source Breakdown Voltage            | $V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$               | 250 | --   | --   | V                   |
| $\Delta BV_{DSS} / \Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D = 250\text{ }\mu\text{A}$ , Referenced to $25^\circ\text{C}$ | --  | 0.22 | --   | V/ $^\circ\text{C}$ |
| $I_{DSS}$                      | Zero Gate Voltage Drain Current           | $V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$                      | --  | --   | 1    | $\mu\text{A}$       |
|                                |                                           | $V_{DS} = 200\text{ V}, T_C = 125^\circ\text{C}$                  | --  | --   | 10   | $\mu\text{A}$       |
| $I_{GSSF}$                     | Gate-Body Leakage Current, Forward        | $V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$                       | --  | --   | 100  | nA                  |
| $I_{GSSR}$                     | Gate-Body Leakage Current, Reverse        | $V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$                      | --  | --   | -100 | nA                  |

**On Characteristics**

|              |                                   |                                                     |     |      |      |          |
|--------------|-----------------------------------|-----------------------------------------------------|-----|------|------|----------|
| $V_{GS(th)}$ | Gate Threshold Voltage            | $V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$     | 3.0 | --   | 5.0  | V        |
| $R_{DS(on)}$ | Static Drain-Source On-Resistance | $V_{GS} = 10\text{ V}, I_D = 1.8\text{ A}$          | --  | 1.38 | 1.75 | $\Omega$ |
| $g_{FS}$     | Forward Transconductance          | $V_{DS} = 50\text{ V}, I_D = 1.8\text{ A}$ (Note 4) | --  | 2.5  | --   | S        |

**Dynamic Characteristics**

|           |                              |                                                                      |    |     |     |    |
|-----------|------------------------------|----------------------------------------------------------------------|----|-----|-----|----|
| $C_{iss}$ | Input Capacitance            | $V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$<br>$f = 1.0\text{ MHz}$ | -- | 155 | 200 | pF |
| $C_{oss}$ | Output Capacitance           |                                                                      | -- | 35  | 45  | pF |
| $C_{rss}$ | Reverse Transfer Capacitance |                                                                      | -- | 4.8 | 6.5 | pF |

**Switching Characteristics**

|              |                     |                                                                                         |    |     |     |    |
|--------------|---------------------|-----------------------------------------------------------------------------------------|----|-----|-----|----|
| $t_{d(on)}$  | Turn-On Delay Time  | $V_{DD} = 125\text{ V}, I_D = 3.6\text{ A},$<br>$R_G = 25\text{ }\Omega$<br>(Note 4, 5) | -- | 6.8 | 25  | ns |
| $t_r$        | Turn-On Rise Time   |                                                                                         | -- | 45  | 100 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time |                                                                                         | -- | 6.4 | 25  | ns |
| $t_f$        | Turn-Off Fall Time  |                                                                                         | -- | 22  | 55  | ns |
| $Q_g$        | Total Gate Charge   | $V_{DS} = 200\text{ V}, I_D = 3.6\text{ A},$<br>$V_{GS} = 10\text{ V}$<br>(Note 4, 5)   | -- | 4.3 | 5.6 | nC |
| $Q_{gs}$     | Gate-Source Charge  |                                                                                         | -- | 1.3 | --  | nC |
| $Q_{gd}$     | Gate-Drain Charge   |                                                                                         | -- | 2.1 | --  | nC |

**Drain-Source Diode Characteristics and Maximum Ratings**

|                 |                                                       |                                                                                            |    |      |      |    |
|-----------------|-------------------------------------------------------|--------------------------------------------------------------------------------------------|----|------|------|----|
| I <sub>S</sub>  | Maximum Continuous Drain-Source Diode Forward Current |                                                                                            | -- | --   | 3.6  | A  |
| I <sub>SM</sub> | Maximum Pulsed Drain-Source Diode Forward Current     |                                                                                            | -- | --   | 14.4 | A  |
| V <sub>SD</sub> | Drain-Source Diode Forward Voltage                    | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 3.6 A                                              | -- | --   | 1.5  | V  |
| t <sub>rr</sub> | Reverse Recovery Time                                 | V <sub>GS</sub> = 0 V, I <sub>S</sub> = 3.6 A,<br>dI <sub>F</sub> / dt = 100 A/μs (Note 4) | -- | 110  | --   | ns |
| Q <sub>rr</sub> | Reverse Recovery Charge                               |                                                                                            | -- | 0.35 | --   | μC |

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 6.4\text{ mH}, I_{AS} = 3.6\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 3.6\text{ A}, di/dt \leq 300\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

# Typical Characteristics

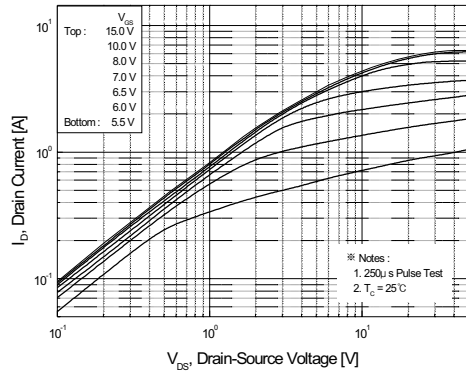


Figure 1. On-Region Characteristics

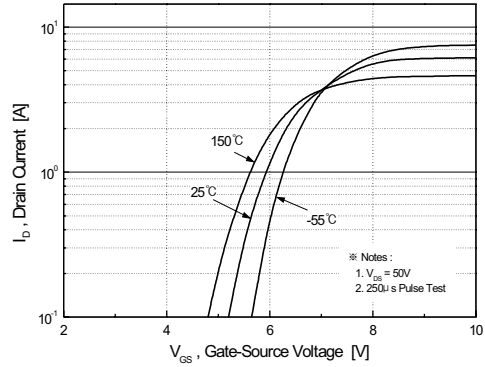


Figure 2. Transfer Characteristics

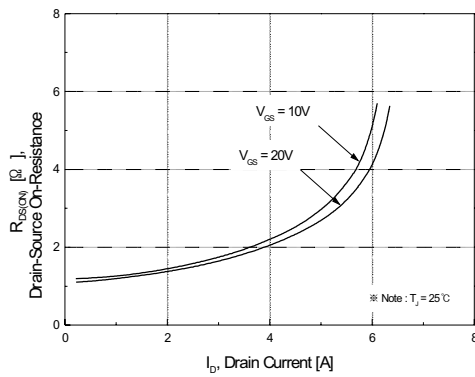


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

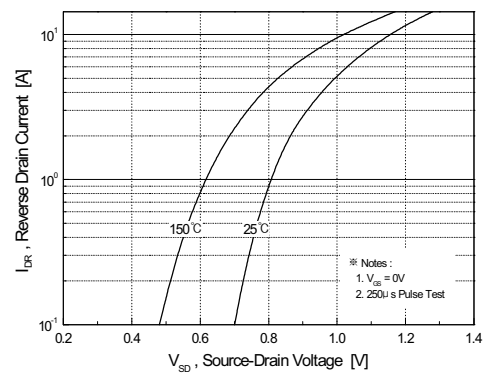


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

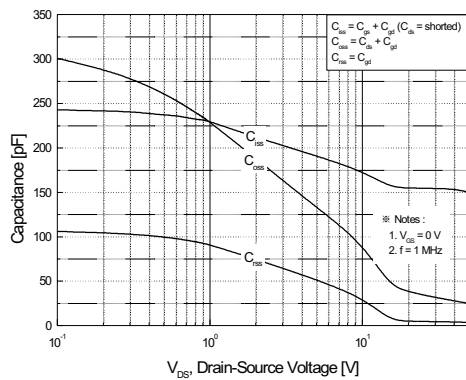


Figure 5. Capacitance Characteristics

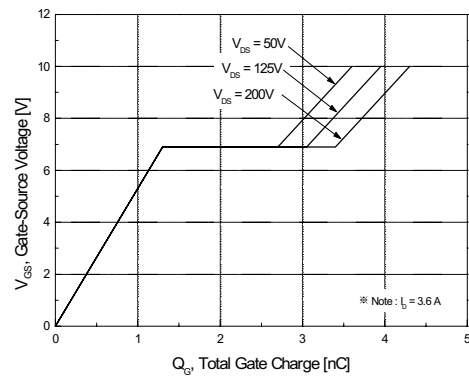
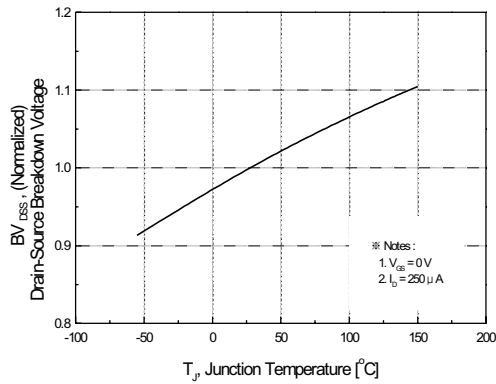
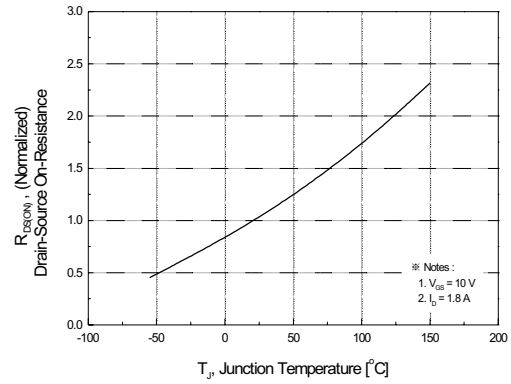


Figure 6. Gate Charge Characteristics

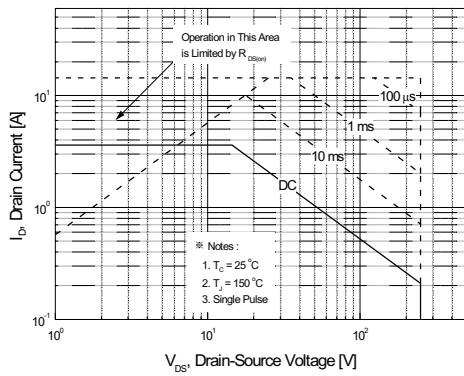
## Typical Characteristics (Continued)



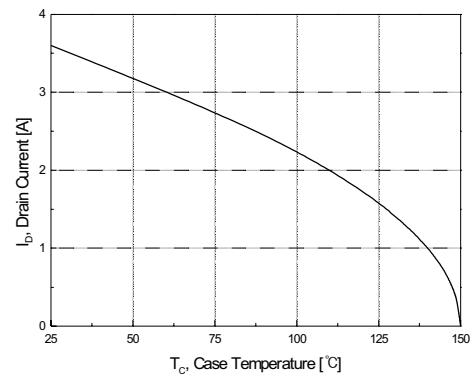
**Figure 7. Breakdown Voltage Variation vs. Temperature**



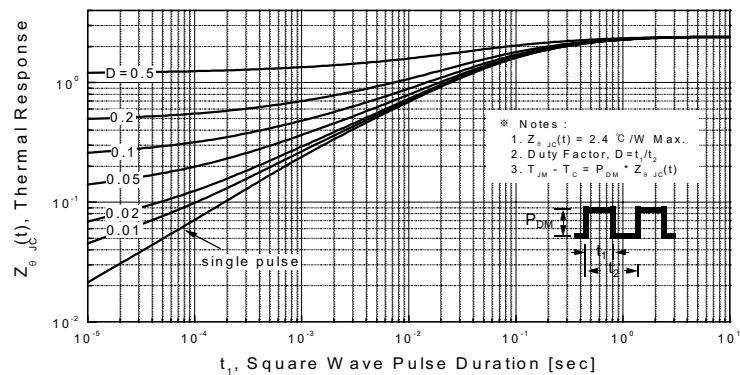
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**

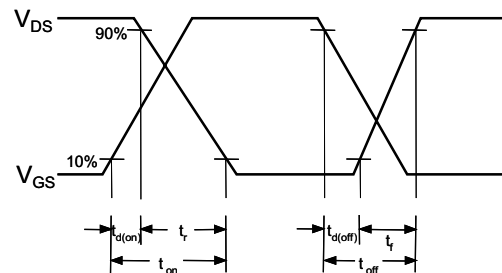


**Figure 11. Transient Thermal Response Curve**

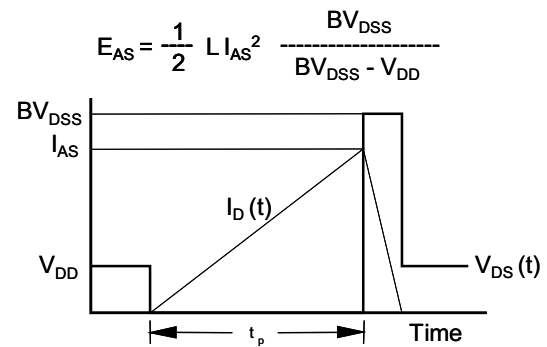
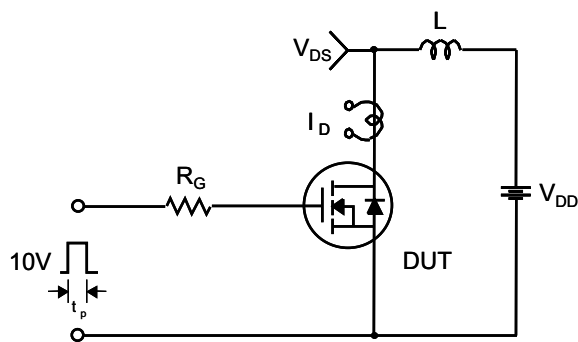
### Gate Charge Test Circuit & Waveform



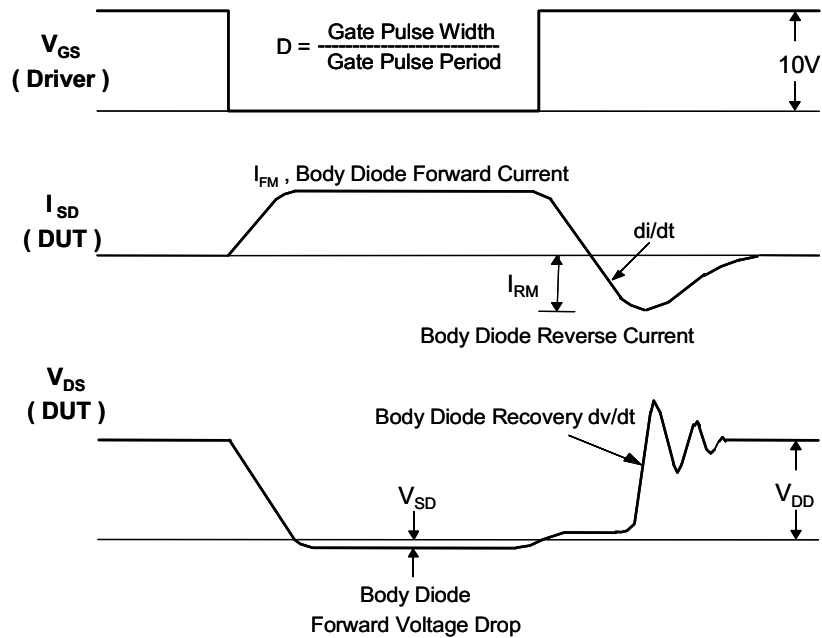
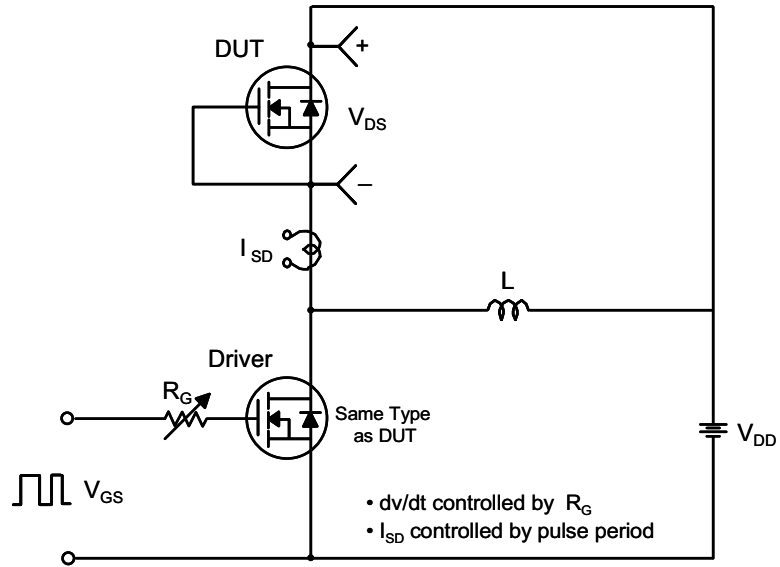
### Resistive Switching Test Circuit & Waveforms



### Unclamped Inductive Switching Test Circuit & Waveforms

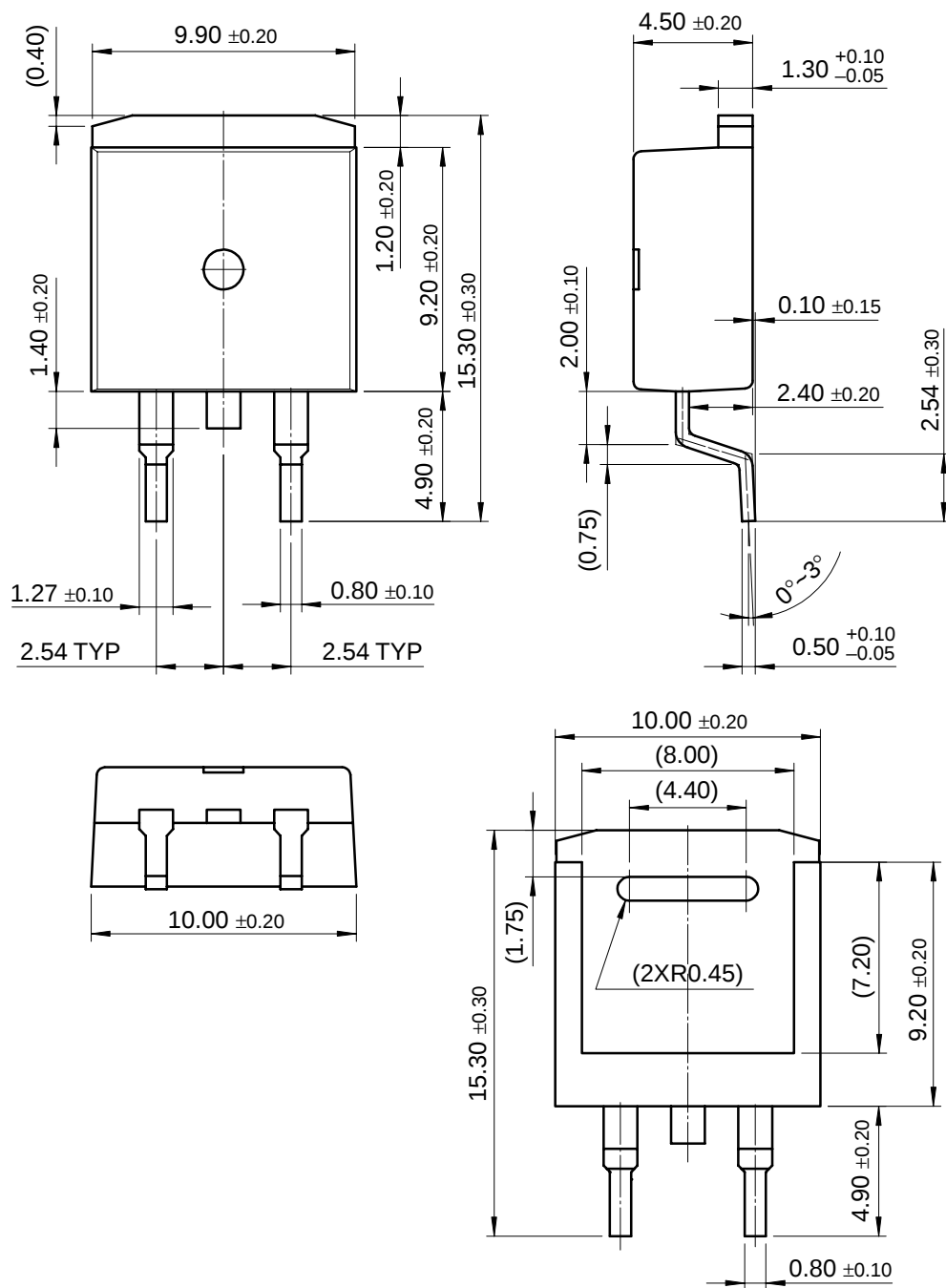


### Peak Diode Recovery dv/dt Test Circuit & Waveforms



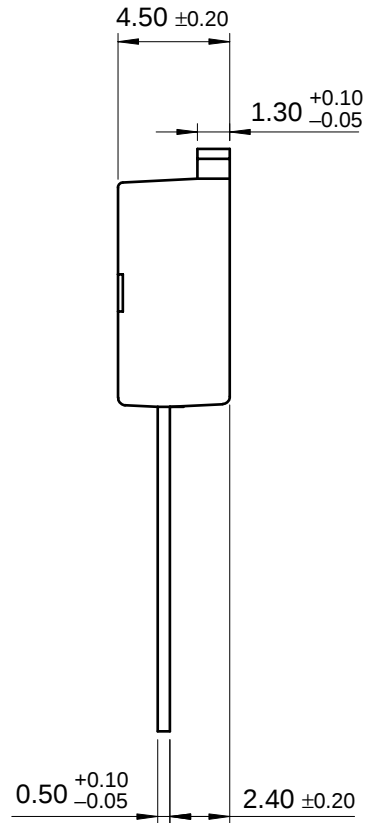
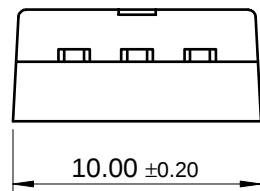
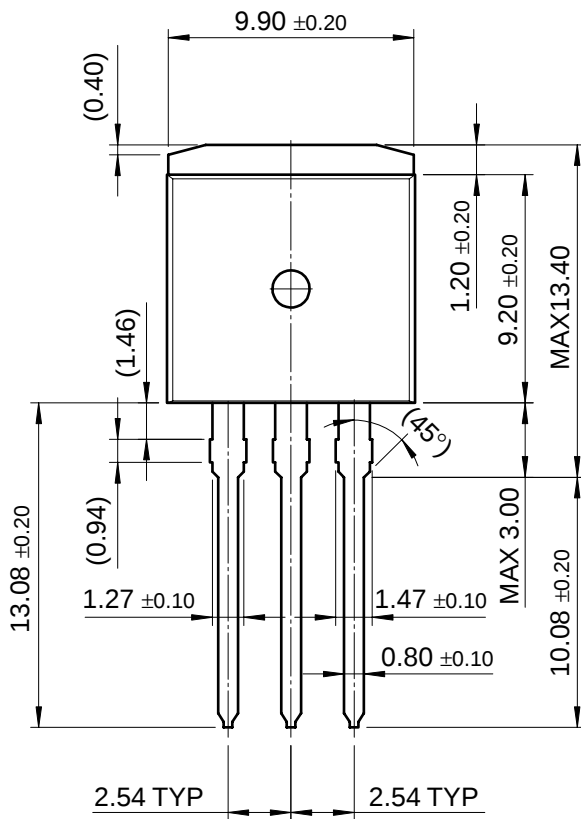
Package Dimensions

D<sup>2</sup>PAK



Package Dimensions (Continued)

I<sup>2</sup>PAK



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